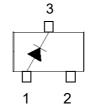
SB411D SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply

Features

- Small surface mounting type.
- High reliability.





SOT-23 Plastic Package

Marking Code: FE

Absolute Maximum Ratings (T_a = 25_°C)

Parameter	Symb I	Value	Unit	
Peak Reverse Voltage	Vrm	40	V	
DC Reverse Voltage	VR	20	V	
Mean Rectifying Current	lo	0.5	А	
Peak Forward Surge Current ¹⁾	FSM	3	А	
Junction Temperature	T _i	125	°C	
Storage Temperature Range	Ts	-40 to +125	₀C	

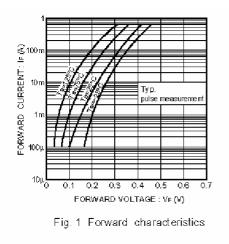
¹⁾60Hz for 1 \bigcirc

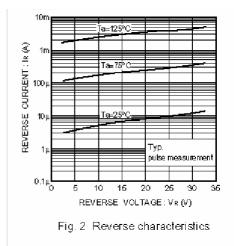
Characteristics at T_a = 25_°C

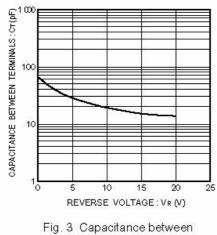
Parameter	Symbol	Min	Тур	Max	Unit
Forward Voltage					
at I _F = 10mA	V _F	-	-	0.3	V
at I _F = 500mA		-	-	0.5	
Reverse Current	1_			20	
at V _R =10V	IR	-	-	30	μA
Capacitance Between Terminals	C -		20		~~
at V _R =10V, f=1MHz	CT	-	20	-	pF



Typical Characteristics







terminals characteristic



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

